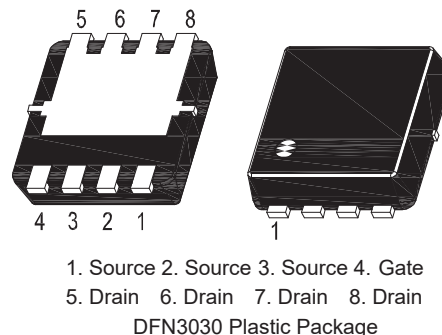
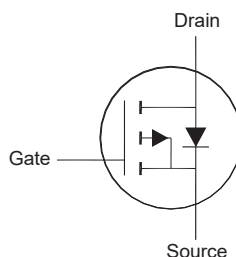


## P-Channel Enhancement Mode MOSFET

### Features

- AEC-Q101 Qualified
- Surface-mounted package
- Low Gate-Source Threshold Voltage
- Halogen and Antimony Free(HAF), RoHS compliant



### Key Parameters

| Parameter         | Value                   | Unit       |
|-------------------|-------------------------|------------|
| $-BV_{DS}$        | 100                     | V          |
| $R_{DS(ON)}$ Max  | 140 @ $-V_{GS} = 10$ V  | m $\Omega$ |
|                   | 150 @ $-V_{GS} = 4.5$ V |            |
| $-V_{GS(th)}$ typ | 1.7                     | V          |
| $Q_g$ typ         | 31.3 @ $-V_{GS} = 10$ V | nC         |

### Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

| Parameter                                        | Symbol         | Value         | Unit             |
|--------------------------------------------------|----------------|---------------|------------------|
| Drain-Source Voltage                             | $-V_{DS}$      | 100           | V                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$      | V                |
| Drain Current                                    | $-I_D$         | 11<br>7       | A                |
| Peak Drain Current, Pulsed <sup>1)</sup>         | $-I_{DM}$      | 40            | A                |
| Single-Pulse Avalanche Current                   | $-I_{AS}$      | 8.4           | A                |
| Single-Pulse Avalanche Energy <sup>2)</sup>      | $E_{AS}$       | 17.6          | mJ               |
| Power Dissipation                                | $P_D$          | 29.7          | W                |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to + 150 | $^\circ\text{C}$ |

### Thermal Characteristics

| Parameter                                                 | Symbol          | Max. | Unit               |
|-----------------------------------------------------------|-----------------|------|--------------------|
| Thermal Resistance from Junction to Case                  | $R_{\theta JC}$ | 4.2  | $^\circ\text{C/W}$ |
| Thermal Resistance from Junction to Ambient <sup>3)</sup> | $R_{\theta JA}$ | 62.5 | $^\circ\text{C/W}$ |

<sup>1)</sup> Pulse Test: Pulse Width  $\leq 100$   $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ , Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ\text{C}$ .

<sup>2)</sup> Limited by  $T_{J(MAX)}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5$  mH,  $R_g = 25$   $\Omega$ ,  $-I_{AS} = 8.4$  A,  $-V_{GS} = 10$  V.

<sup>3)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at  $T_a = 25^\circ\text{C}$  unless otherwise specified

| Parameter                                                                                                                                                                            | Symbol        | Min.   | Typ.         | Max.       | Unit          |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|--------------|------------|---------------|
| <b>STATIC PARAMETERS</b>                                                                                                                                                             |               |        |              |            |               |
| Drain-Source Breakdown Voltage<br>at $-I_D = 250\ \mu\text{A}$                                                                                                                       | $-BV_{DSS}$   | 100    | -            | -          | V             |
| Drain-Source Leakage Current<br>at $-V_{DS} = 100\ \text{V}$                                                                                                                         | $-I_{DSS}$    | -      | -            | 1          | $\mu\text{A}$ |
| Gate Leakage Current<br>at $V_{GS} = \pm 20\ \text{V}$                                                                                                                               | $I_{GSS}$     | -      | -            | $\pm 100$  | nA            |
| Gate-Source Threshold Voltage<br>at $V_{DS} = V_{GS}$ , $-I_D = 250\ \mu\text{A}$                                                                                                    | $-V_{GS(th)}$ | 1.2    | -            | 2.5        | V             |
| Drain-Source On-State Resistance<br>at $-V_{GS} = 10\ \text{V}$ , $-I_D = 6\ \text{A}$<br>at $-V_{GS} = 4.5\ \text{V}$ , $-I_D = 5\ \text{A}$                                        | $R_{DS(on)}$  | -<br>- | 110<br>-     | 140<br>150 | m $\Omega$    |
| <b>DYNAMIC PARAMETERS</b>                                                                                                                                                            |               |        |              |            |               |
| Forward Transconductance<br>at $-V_{DS} = 5\ \text{V}$ , $-I_D = 5\ \text{A}$                                                                                                        | $g_{fs}$      | -      | 16.3         | -          | S             |
| Gate Resistance<br>at $V_{GS} = 0\ \text{V}$ , $V_{DS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                          | $R_g$         | -      | 4.8          | -          | $\Omega$      |
| Input Capacitance<br>at $-V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                      | $C_{iss}$     | -      | 1785         | -          | pF            |
| Output Capacitance<br>at $-V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                                                     | $C_{oss}$     | -      | 56           | -          | pF            |
| Reverse Transfer Capacitance<br>at $-V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$                                                                           | $C_{rss}$     | -      | 12           | -          | pF            |
| Total Gate Charge<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DS} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$<br>at $-V_{GS} = 4.5\ \text{V}$ , $-V_{DS} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$ | $Q_g$         | -<br>- | 31.3<br>14.6 | -<br>-     | nC            |
| Gate-Source Charge<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DS} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$                                                                                  | $Q_{gs}$      | -      | 6.3          | -          | nC            |
| Gate-Drain Charge<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DS} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$                                                                                   | $Q_{gd}$      | -      | 4.9          | -          | nC            |
| Turn-On Delay Time<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DD} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$ , $R_g = 3.3\ \Omega$                                                            | $t_{d(on)}$   | -      | 11           | -          | ns            |
| Turn-On Rise Time<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DD} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$ , $R_g = 3.3\ \Omega$                                                             | $t_r$         | -      | 4            | -          | ns            |
| Turn-Off Delay Time<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DD} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$ , $R_g = 3.3\ \Omega$                                                           | $t_{d(off)}$  | -      | 21           | -          | ns            |
| Turn-Off Fall Time<br>at $-V_{GS} = 10\ \text{V}$ , $-V_{DD} = 50\ \text{V}$ , $-I_D = 6\ \text{A}$ , $R_g = 3.3\ \Omega$                                                            | $t_f$         | -      | 4            | -          | ns            |
| <b>Body-Diode PARAMETERS</b>                                                                                                                                                         |               |        |              |            |               |
| Drain-Source Diode Forward Voltage<br>at $-I_S = 1\ \text{A}$ , $V_{GS} = 0\ \text{V}$                                                                                               | $-V_{SD}$     | -      | -            | 1.2        | V             |
| Body-Diode Continuous Current                                                                                                                                                        | $-I_S$        | -      | -            | 11         | A             |
| Body-Diode Continuous Current, Pulsed                                                                                                                                                | $-I_{SM}$     | -      | -            | 40         | A             |
| Body Diode Reverse Recovery Time<br>at $-I_S = 6\ \text{A}$ , $di/dt = 100\ \text{A} / \mu\text{s}$                                                                                  | $t_{rr}$      | -      | 21           | -          | ns            |
| Body Diode Reverse Recovery Charge<br>at $-I_S = 6\ \text{A}$ , $di/dt = 100\ \text{A} / \mu\text{s}$                                                                                | $Q_{rr}$      | -      | 23           | -          | nC            |

## Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

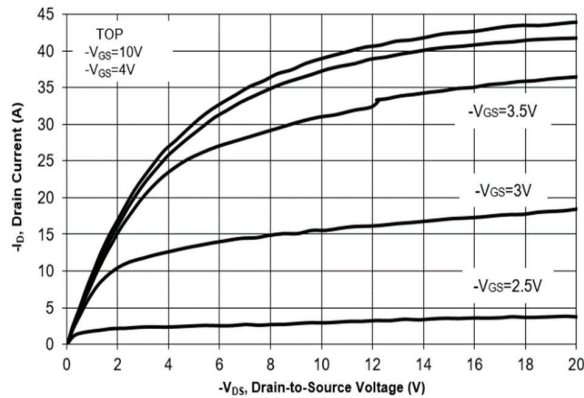


Fig. 2 Typical Transfer Characteristics

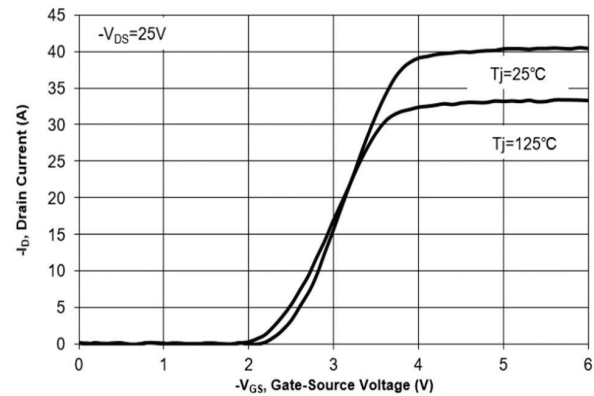


Fig. 3 on-Resistance vs. Drain Current

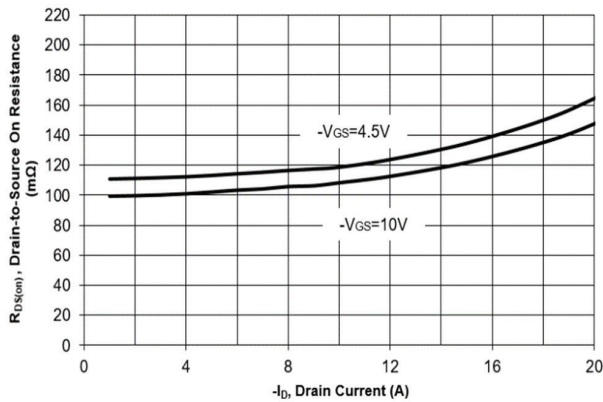


Fig. 4 on-Resistance vs. Gate to Source Voltage

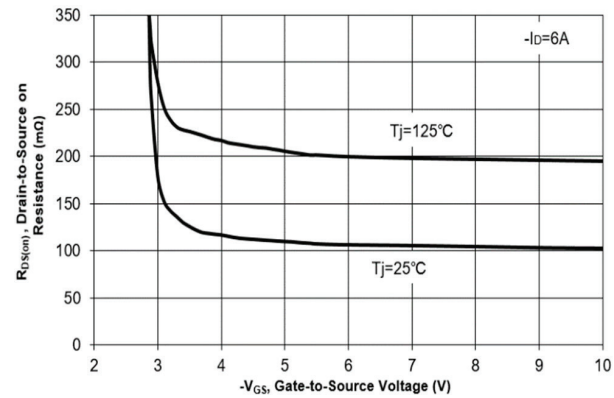


Fig. 5 on-Resistance vs. T<sub>j</sub>

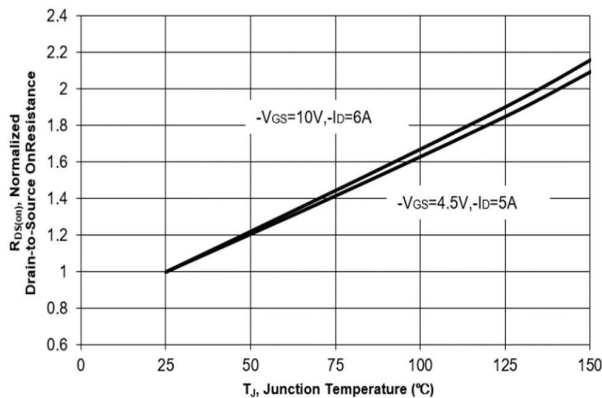
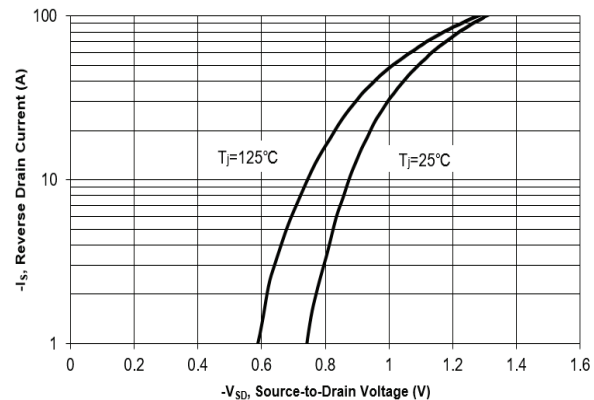


Fig. 6 Typical Body-Diode Forward Characteristics



## Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

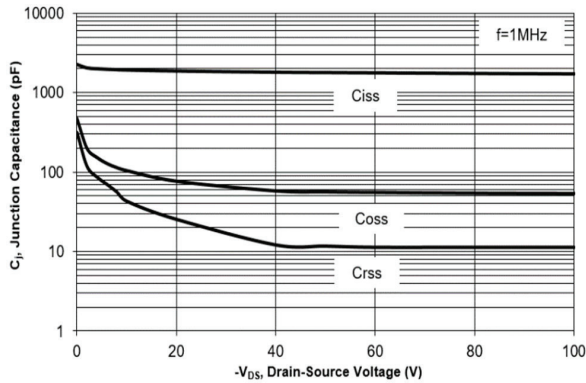


Fig. 8 Drain-Source Leakage Current vs.  $T_J$

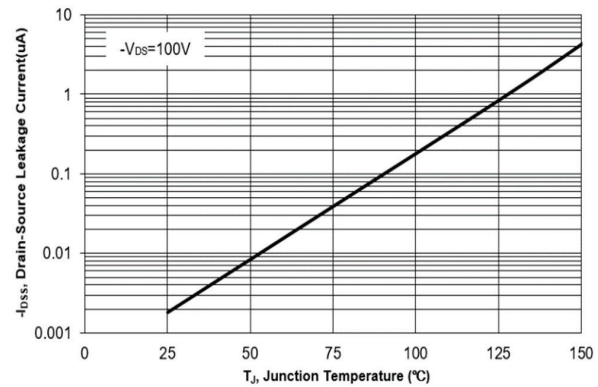


Fig. 9  $V_{(BR)DSS}$  vs. Junction Temperature

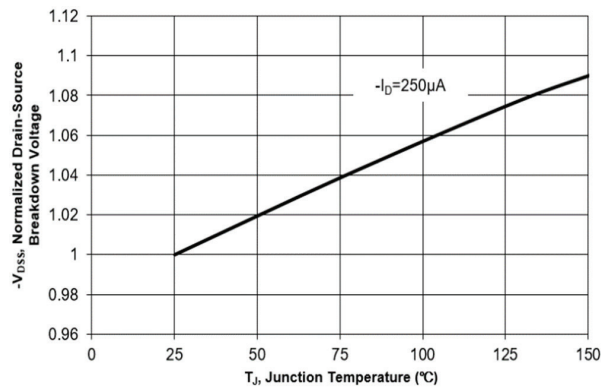


Fig. 10 Gate Threshold Variation vs.  $T_J$

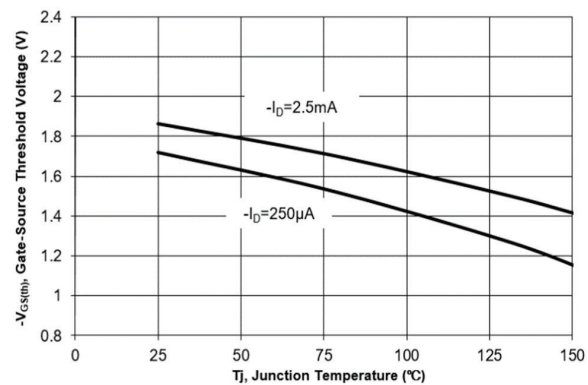


Fig. 11 Gate Charge

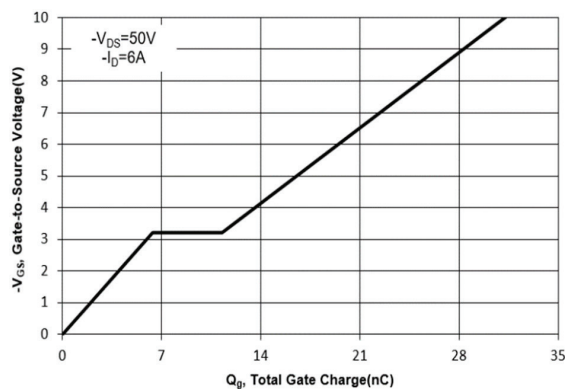
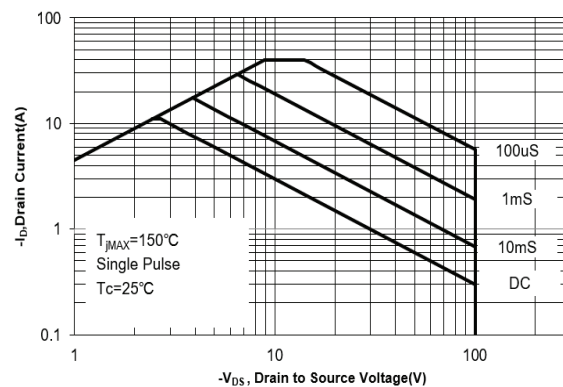


Fig. 12 Safe Operation Area



## Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JC}$ )

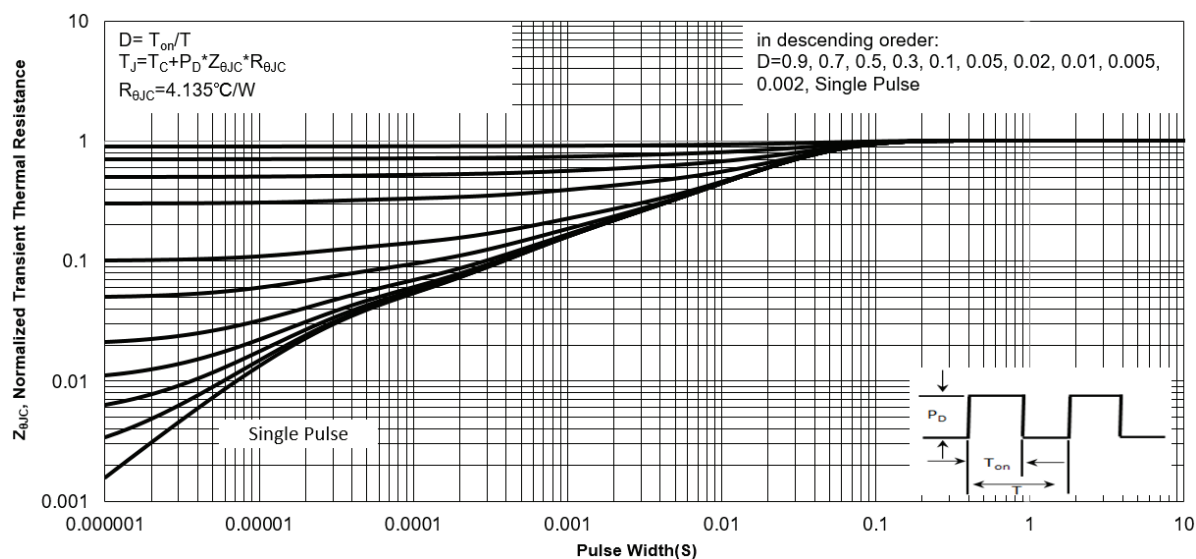
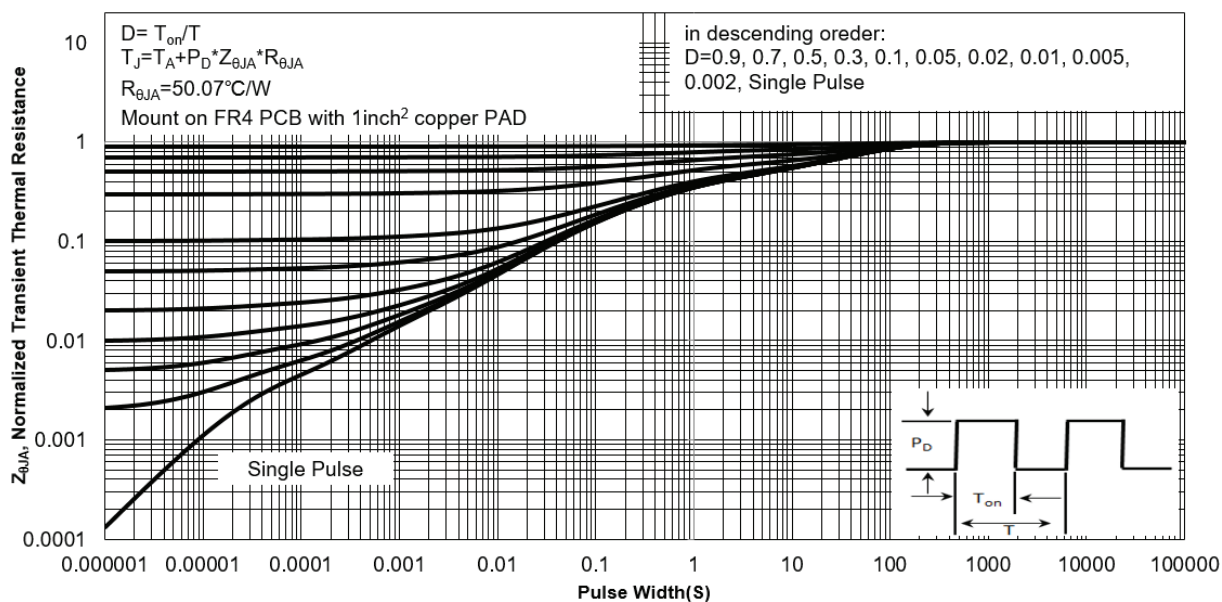


Fig. 14 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JA}$ )



## Test Circuits

Fig.1-1 Switching times test circuit

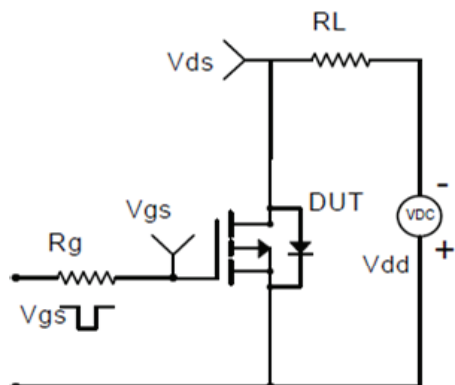


Fig.1-2 Switching Waveform

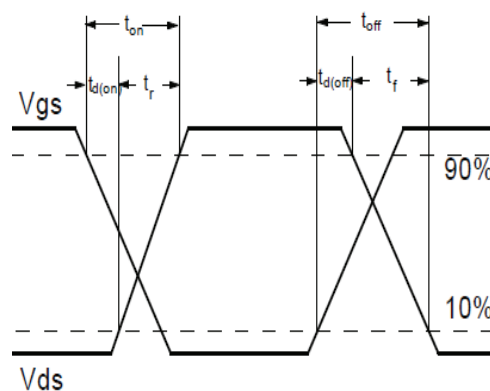


Fig.2-1 Gate charge test circuit

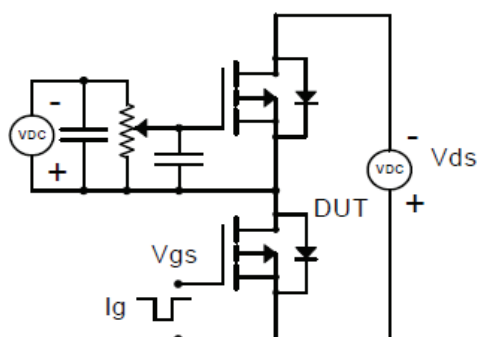


Fig.2-2 Gate charge waveform

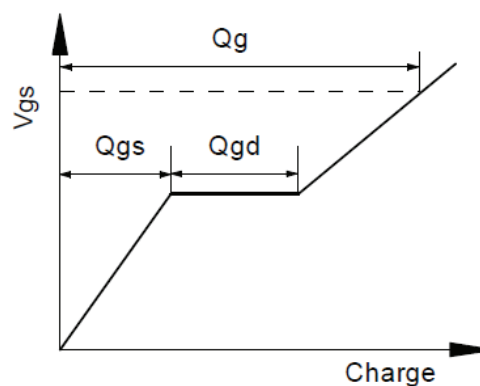


Fig.3-1 Avalanche test circuit

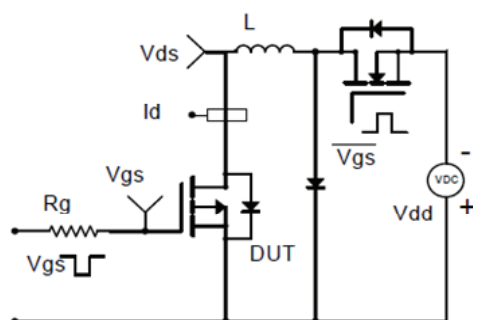
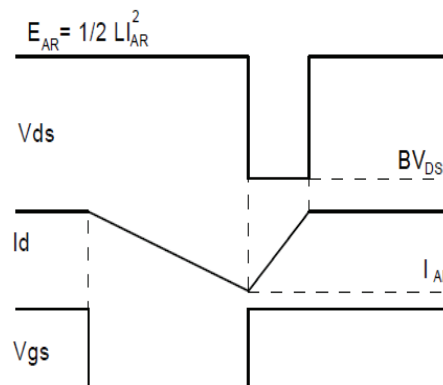
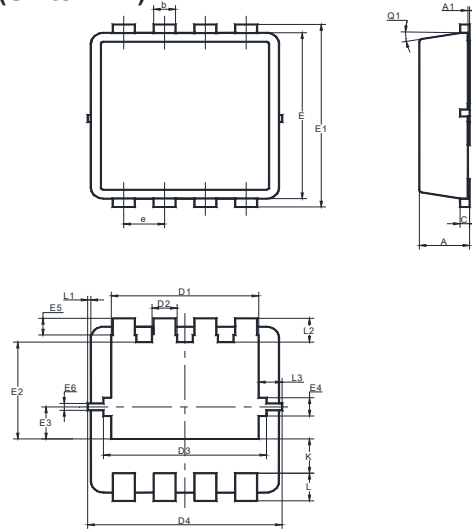


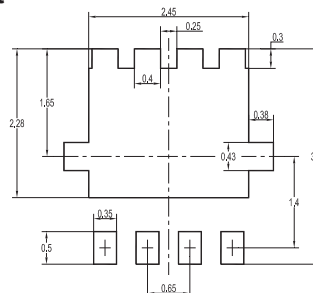
Fig.3-2 Avalanche waveform



**Package Outline Dimensions (Units: mm)**
**DFN3030**


| UNIT | A   | A1   | b    | c    | D1  | D2  | D3  | D4  | E   | E1  | E2   | E3   | E4   |
|------|-----|------|------|------|-----|-----|-----|-----|-----|-----|------|------|------|
| mm   | 0.9 | 0.05 | 0.35 | 0.25 | 2.6 | 0.5 | 2.7 | 3.2 | 3.1 | 3.3 | 1.85 | 0.68 | 0.43 |
|      | 0.7 | 0    | 0.24 | 0.1  | 2.4 | 0.3 | 2.5 | 3   | 2.9 | 3.1 | 1.65 | 0.48 | 0.23 |

| UNIT | E5  | E6   | e   | K    | L   | L1  | L2   | L3    | θ1  |
|------|-----|------|-----|------|-----|-----|------|-------|-----|
| mm   | 0.4 | 0.25 | 0.7 | 0.72 | 0.5 | 0.1 | 0.53 | 0.475 | 12° |
|      | 0.2 | 0.15 | 0.6 | 0.52 | 0.3 | 0   | 0.33 | 0.275 | 0°  |

**Recommended Soldering Footprint**

**Packing information**

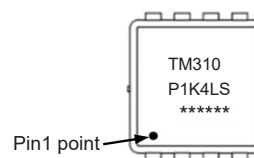
| Package | Tape Width (mm) | Pitch   |               | Reel Size |      | Per Reel Packing Quantity |
|---------|-----------------|---------|---------------|-----------|------|---------------------------|
|         |                 | mm      | inch          | mm        | inch |                           |
| DFN3030 | 12              | 8 ± 0.1 | 0.315 ± 0.004 | 330       | 13   | 5,000                     |

**Marking information**

" TM310P1K4LS " = Part No.

" \*\*\*\*\* " = Date Code Marking

Font type: Arial



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